MICROWAVE POWER GaAs FET TIM5867-30UL

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET ·HIGH POWER
- P1dB= 45.0dBm at 5.85GHz to 6.75GHz

·HIGH GAIN

G1dB= 10.0dB at 5.85GHz to 6.75GHz

- **·LOW INTERMODULATION DISTORTION**
- IM3= -45dBc at Pout= 34dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS SYMBOL CONDITIONS UNIT MIN. TYP. MAX. Output Power at 1dB 45.0 Gain Compression Point P1dB dBm 44.0 Power Gain at 1dB G1dB 9.0 10.0 dB Gain Compression Point **VDS= 10V** IDSset= 6.4A **Drain Current** IDS1 А 7.0 8.0 f= 5.85 to 6.75GHz Gain Flatness ΔG dB ± 0.8 Power Added Efficiency % 41 ηadd 3rd Order Intermodulation **Two-Tone Test** IM3 dBc -44 -47 Distortion ____ Po= 34dBm, ∆f= 5MHz (Single Carrier Level) Drain Current IDS2 А 7.0 8.0 $(VDS \times IDS + Pin - P1dB)$ °C **Channel Temperature Rise** ΔTch 100 × Rth(c-c)

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 10.0A	S	_	8.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 80mA	V	-0.5	-2.0	-3.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А	_	16.0	
Gate-Source Breakdown Voltage	VGSO	IGS= -240µA	V	-5	_	
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.0	1.5

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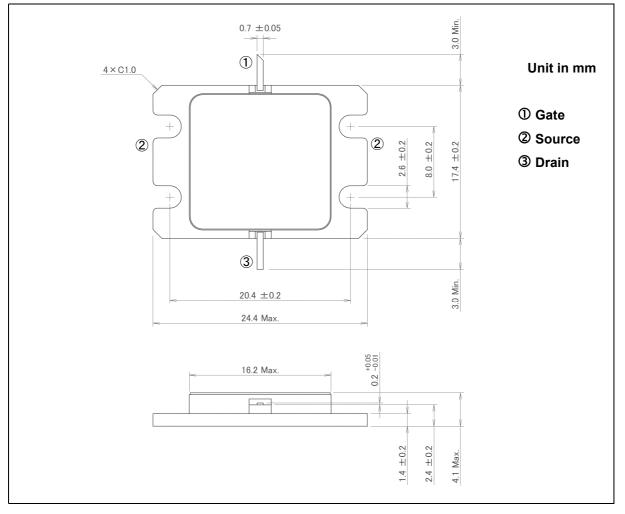
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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	18.0
Total Power Dissipation (Tc= 25°C)	PT	W	100
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA05A)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

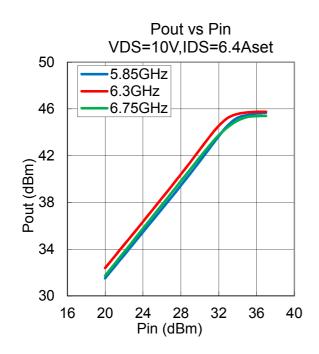
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

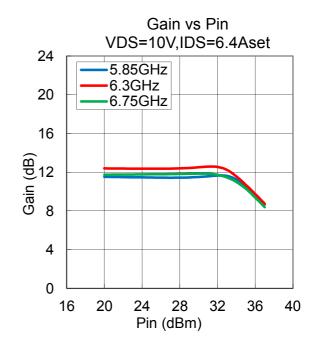
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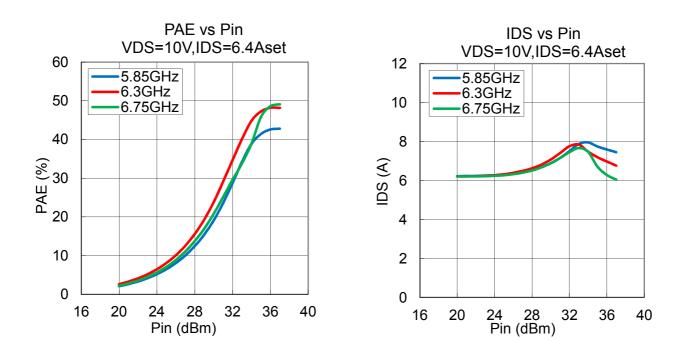
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout, Gain, PAE, IDS vs. Pin

VDS= 10 V, IDSset= 6.4 A, f= 5.85, 6.3, 6.75 GHz, Ta= +25 °C





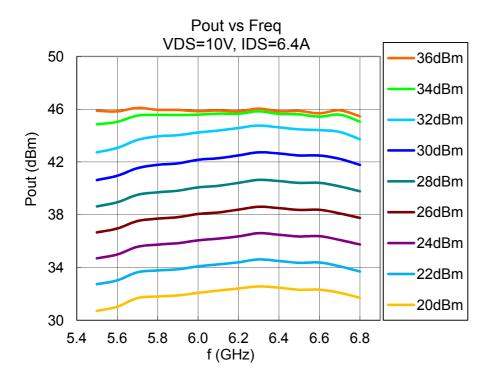


- MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout vs. Frequency

VDS= 10 V, IDSset= 6.4 A, Ta= +25 °C



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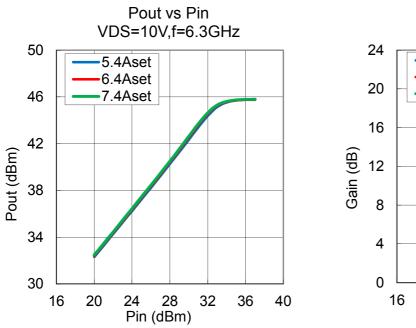
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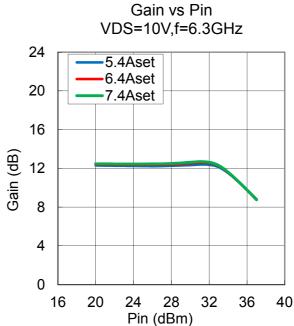
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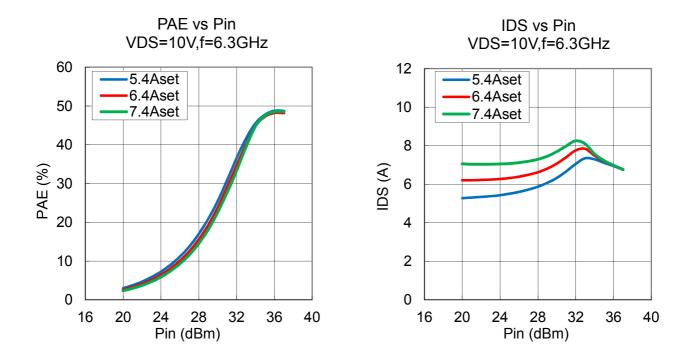
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout, Gain, PAE, IDS vs. Pin vs. IDSset

VDS= 10 V, IDSset= 5.4, 6.4, 7.4. A, f= 6.3 GHz, Ta= +25 °C







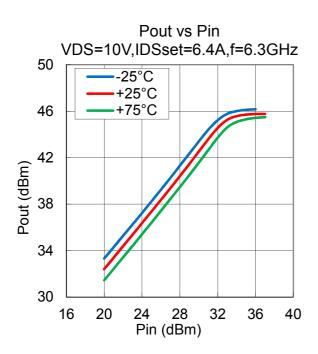
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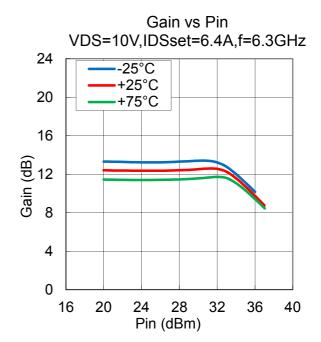
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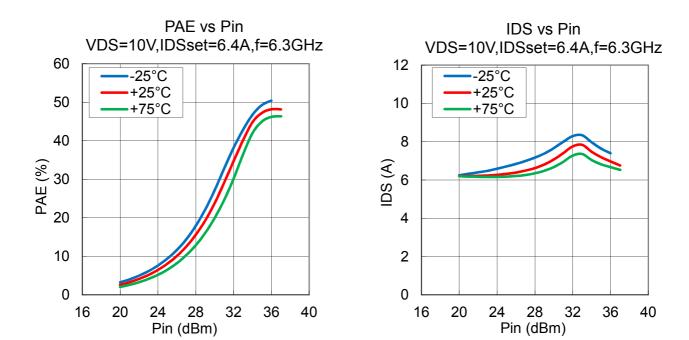
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout, Gain, PAE, IDS vs. Pin vs. Temperature

VDS= 10 V, IDSset= 6.4 A, f= 6.3 GHz, Ta= -25, +25, +75 °C







MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA RESTRICTIONS ON PRODUCT USE

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